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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete If Known	
Sheet	1	of	1	Application Number	10/091,338
				Filing Date	March 6, 2002
				First Named Inventor	Toru MITSUKI et al.
				Group Art Unit	2824
				Examiner Name	Bradley Smith
				Attorney Docket Number	0756-2448

U.S. PATENT DOCUMENTS						
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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FOREIGN PATENT DOCUMENTS								
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		Office ³	Number ⁴	Kind Code ² (if known)				
BKS ↓ ✓		JP	07-162004			06/23/1995		AB
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OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
73/15		H. Koseki et al., <i>Recent Progress of Low Temperature Poly-Si Technology</i> , Electronic Display Forum, Pages 4-31 to 4-38 and English Translation, Pages 1-21, April 15, 1999.	
73/15		Kenji Sera et al., <i>Uniformity Improvement of Excimer Laser Crystallized Poly-Si Thin Film Transistors</i> , AM-LCD '96/IDM '96, Pages 85-88.	
73/15		M. Bonnel et al., <i>Polycrystalline Silicon Thin-Film Transistors with Two-Step Annealing Process</i> , IEEE Electron Device Letters, Vol. 14, No. 12, Pages 551-553, December 1993.	
73/15		M. Fuse et al., <i>Performance of Poly-Si Thin Film Transistors Fabricated by Excimer- Laser Annealing of SiH₄ and Si₂H₆ Source Low Pressure Vapor Deposited α-Si Films With or Without Solid-Phase Crystallization</i> , Solid State Phenomena, Vols. 37-38, Pages 565-570, 1994.	

Examiner Signature	<i>73/15</i>	Date Considered	6/15/04
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